



YOUSHANG SEMICONDUCTOR

**设计研发新型功率器件**

**各类小信号开关**

**中低压及高压大电流等场效应管**

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企业QQ二维码

## Features

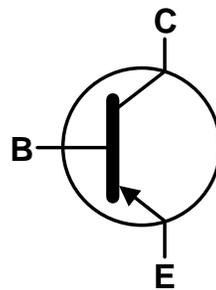
- Epitaxial Planar Die Construction
- Ideal for Medium Power Amplification and Switching
- Complementary NPN Type: DIODES NK-MMBT4401

## Mechanical Data

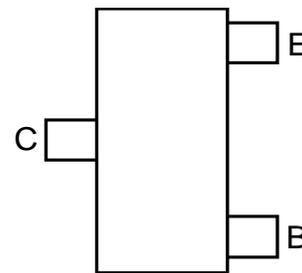
- Package: SOT23
- Package Material: Molded Plastic "Green" Compound  
UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads, Solderable per  
MIL-STD-202, Method 208 ③
- Weight: 0.008 grams (Approximate)



Top View



Device Symbol



Top View  
Pin-Out

### Absolute Maximum Ratings (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

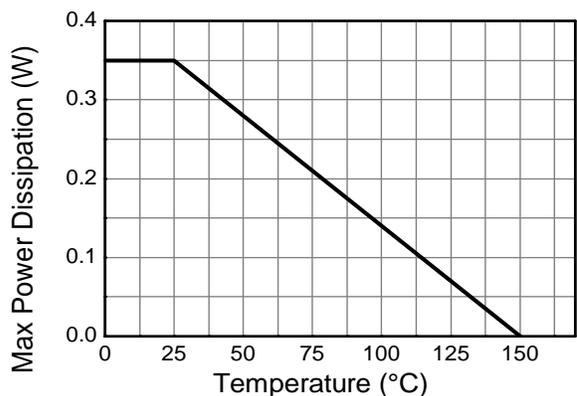
Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CB0}$	-40	V
Collector-Emitter Voltage	$V_{CEO}$	-40	V
Emitter-Base Voltage	$V_{EB0}$	-6	V
Collector Current - Continuous (Note 7)	$I_C$	-600	mA

### Thermal Characteristics (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

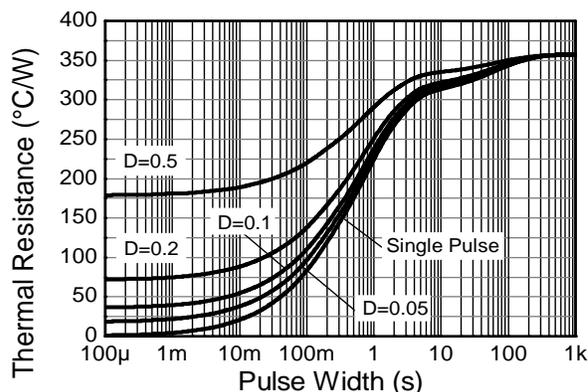
Characteristic	Symbol	Value	Unit
Collector Power Dissipation	$P_D$	310	mW
		(Note 6)	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	(Note 5)	403
		(Note 6)	357
Thermal Resistance, Junction to Leads	$R_{\theta JL}$	350	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	55	$^\circ\text{C/W}$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

Notes: 5. For the device mounted on minimum recommended pad layout FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.  
 6. For the device mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.  
 7. Thermal resistance from junction to solder-point (at the end of the collector lead).

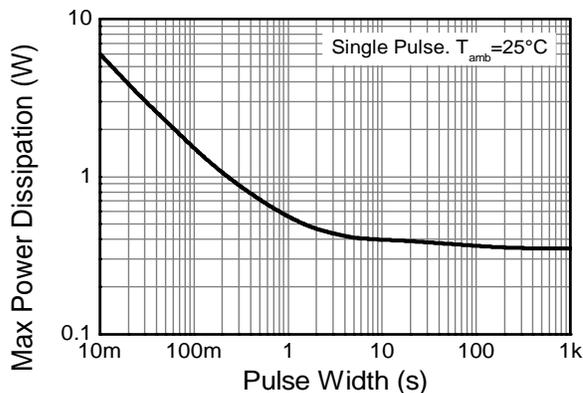
### Thermal Characteristics and Derating Information



**Derating Curve**



**Transient Thermal Impedance**



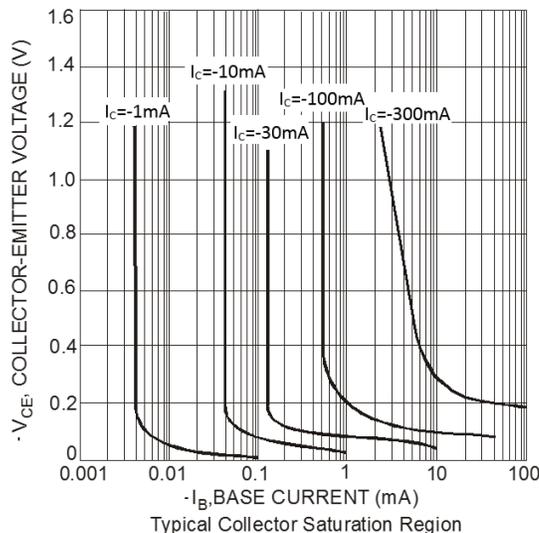
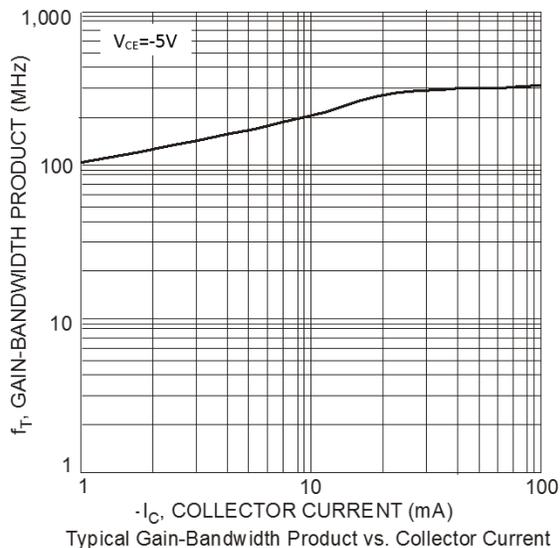
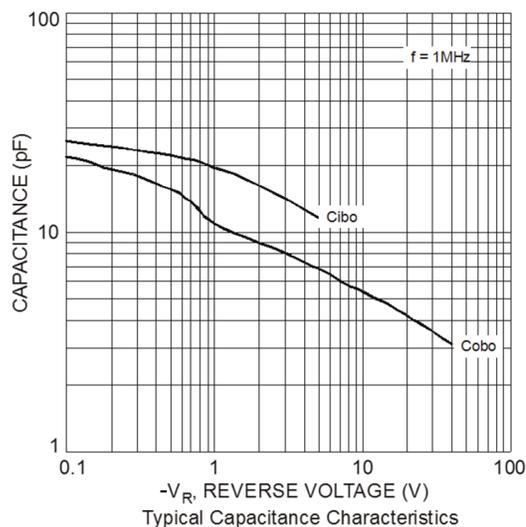
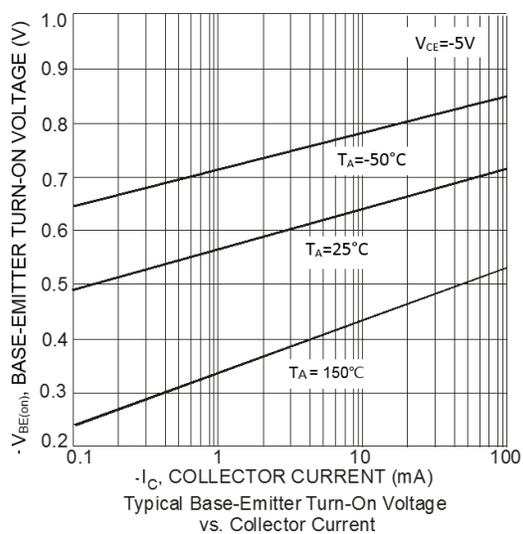
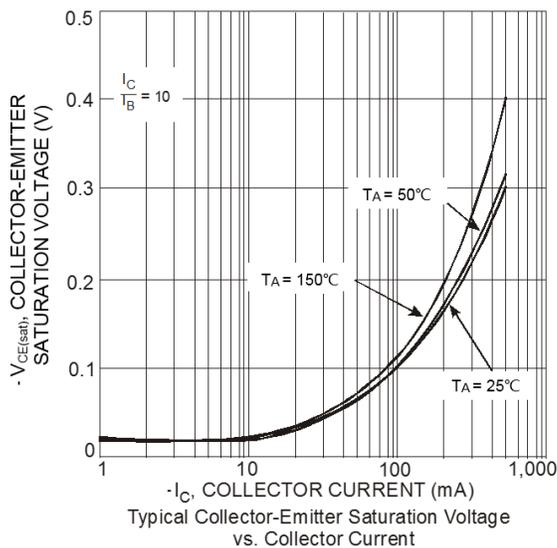
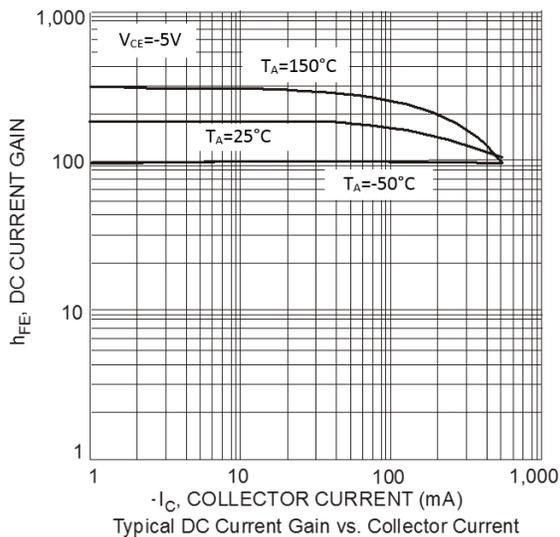
**Pulse Power Dissipation**

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 8)</b>					
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-40	—	V	I <sub>C</sub> = -100μA
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	-40	—	V	I <sub>C</sub> = -10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-6	—	V	I <sub>E</sub> = -100μA
Collector Cutoff Current	I <sub>CEX</sub>	—	-100	nA	V <sub>CE</sub> = -35V, V <sub>EB(off)</sub> = -0.4V
Base Cutoff Current	I <sub>BL</sub>	—	-100	nA	V <sub>CE</sub> = -35V, V <sub>EB(off)</sub> = -0.4V
<b>ON CHARACTERISTICS (Note 8)</b>					
DC Current Gain	h <sub>FE</sub>	30	—	—	I <sub>C</sub> = -100μA, V <sub>CE</sub> = -1V
		60	—		I <sub>C</sub> = -1.0mA, V <sub>CE</sub> = -1V
		100	—		I <sub>C</sub> = -10mA, V <sub>CE</sub> = -1V
		100	300		I <sub>C</sub> = -150mA, V <sub>CE</sub> = -2V
		20	—		I <sub>C</sub> = -500mA, V <sub>CE</sub> = -2V
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	—	-0.40 -0.75	V	I <sub>C</sub> = -150mA, I <sub>B</sub> = -15mA I <sub>C</sub> = -500mA, I <sub>B</sub> = -50mA
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	-0.75 —	-0.95 -1.30	V	I <sub>C</sub> = -150mA, I <sub>B</sub> = -15mA I <sub>C</sub> = -500mA, I <sub>B</sub> = -50mA
<b>SMALL SIGNAL CHARACTERISTICS</b>					
Output Capacitance	C <sub>obo</sub>	—	8.5	pF	V <sub>CB</sub> = -10V, f = 1.0MHz, I <sub>E</sub> = 0
Input Capacitance	C <sub>ibo</sub>	—	30	pF	V <sub>EB</sub> = -0.5V, f = 1.0MHz, I <sub>C</sub> = 0
Input Impedance	h <sub>ie</sub>	1.5	15	kΩ	V <sub>CE</sub> = -10V, I <sub>C</sub> = -1mA, f = 1kHz
Voltage Feedback Ratio	h <sub>re</sub>	0.1	8.0	x 10 <sup>-4</sup>	
Small Signal Current Gain	h <sub>fe</sub>	60	500	—	
Output Admittance	h <sub>oe</sub>	1.0	100	μS	
Current Gain-Bandwidth Product	f <sub>T</sub>	200	—	MHz	
<b>SWITCHING CHARACTERISTICS</b>					
Delay Time	t <sub>d</sub>	—	15	ns	V <sub>CC</sub> = -30V, I <sub>C</sub> = -150mA, V <sub>BE(off)</sub> = -2V, I <sub>B1</sub> = -15mA
Rise Time	t <sub>r</sub>	—	20	ns	V <sub>CC</sub> = -30V, I <sub>C</sub> = -150mA, I <sub>B1</sub> = -I <sub>B2</sub> = -15mA
Storage Time	t <sub>s</sub>	—	225	ns	
Fall Time	t <sub>f</sub>	—	30	ns	

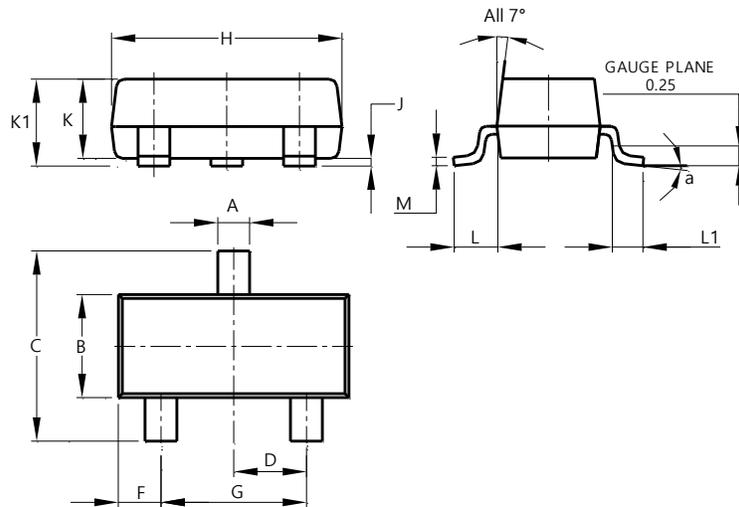
Note: 8. Short duration pulse test used to minimize self-heating effect.

**Typical Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)



## Package Outline Dimensions

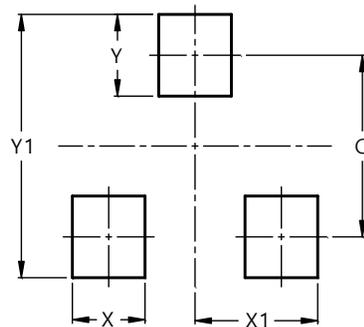
SOT23



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

## Suggested Pad Layout

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9